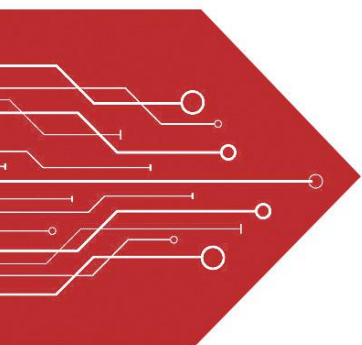


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

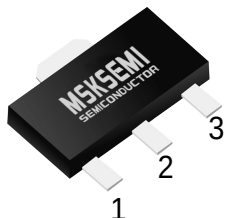
Product data sheet

FEATURES

- High Collector Current
- Complementary to PXT8550

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	1.5	A
P _C	Collector Power Dissipation	0.5	W
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

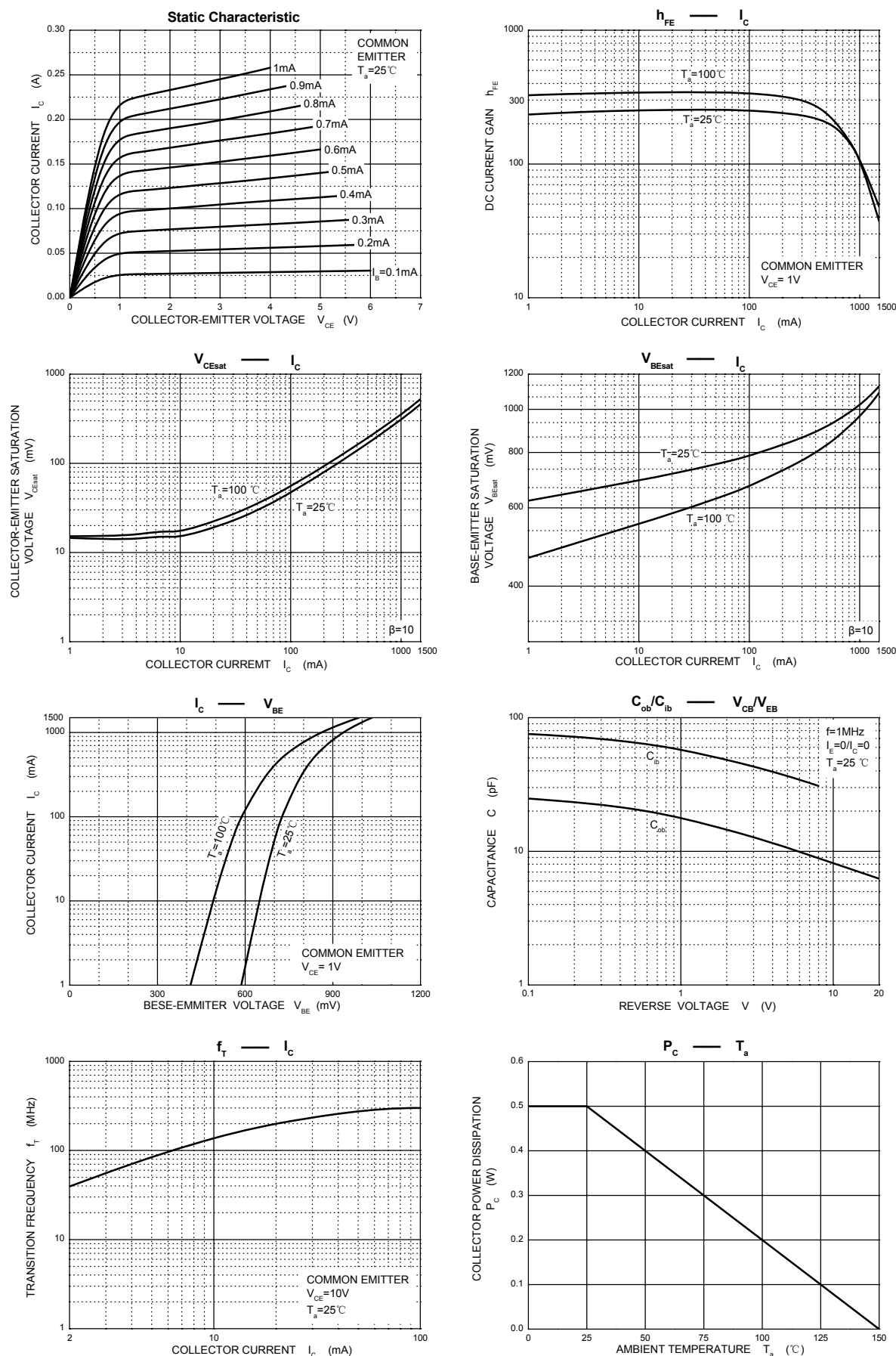
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C = 100mA	120		400	
	h _{FE(2)}	V _{CE} =1V, I _C = 800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B = 80mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =800mA, I _B = 80mA			1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C = 50mA f=30MHz	100			MHz

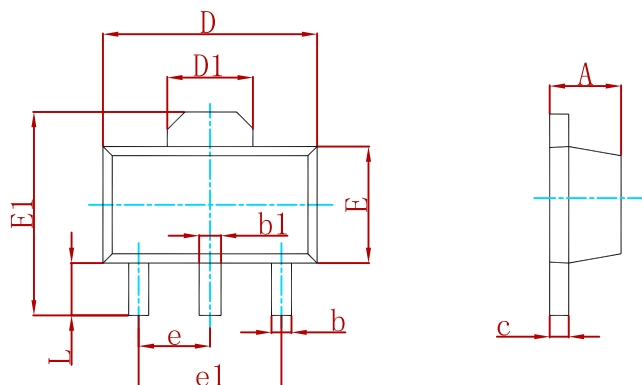
CLASSIFICATION OF h_{FE(1)}

Rank	L	H	J
Range	120-200	200-350	300-400

Typical Characteristics

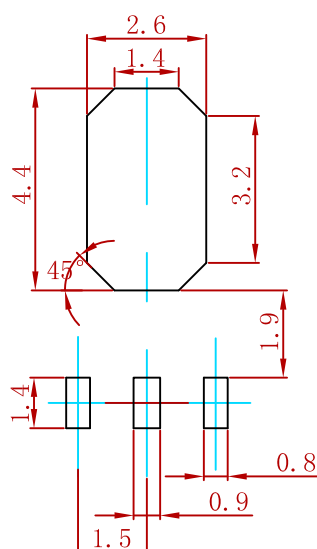


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PXT8050	SOT-89	1000

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